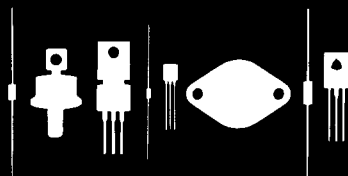


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145 Adams Avenue
Hauppauge, New York 11788



2N6473 2N6474 NPN

2N6475 2N6476 PNP

COMPLEMENTARY SILICON
SWITCHING TRANSISTORS

JEDEC TO-220 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6473 Series types are complementary silicon power transistors manufactured by the epitaxial base process designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	2N6473 2N6475	2N6474 2N6476	UNIT
Collector-Base Voltage	V_{CB0}	110	130	V
Collector-Emitter Voltage ($R_{BE}=100\Omega$)	V_{CER}	110	130	V
Collector-Emitter Voltage	V_{CEO}	100	120	V
Emitter-Base Voltage	V_{EBO}		5.0	V
Collector Current	I_C		4.0	A
Base Current	I_B		2.0	A
Power Dissipation	P_D		40	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +150		$^{\circ}\text{C}$
Thermal Resistance	θ_{JC}		3.125	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6473 2N6475		2N6474 2N6476		UNIT
		MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}$		0.1		0.1	mA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}, T_C=100^{\circ}\text{C}$		2.0		2.0	mA
I_{CER}	$V_{CE}=\text{Rated } V_{CER}, R_{BE}=100\Omega$		0.1		0.1	mA
I_{CER}	$V_{CE}=\text{Rated } V_{CER}, R_{BE}=100\Omega, T_C=100^{\circ}\text{C}$		2.0		2.0	mA
I_{CEO}	$V_{CE}=\frac{1}{2} \text{ Rated } V_{CEO}$		1.0		1.0	mA
I_{EBO}	$V_{BE}=5.0\text{V}$		1.0		1.0	mA
BV_{CEO}	$I_C=100\text{mA}$	100		120		V
BV_{CER}	$I_C=100\text{mA}, R_{BE}=100\Omega$	110		130		V
$V_{CE}(\text{SAT})$	$I_C=1.5\text{A}, I_B=0.15\text{A}$		1.2		1.2	V
$V_{CE}(\text{SAT})$	$I_C=4.0\text{A}, I_B=2.0\text{A}$		2.5		2.5	V
$V_{BE}(\text{ON})$	$V_{CE}=4.0\text{V}, I_C=1.5\text{A}$		2.0		2.0	V
$V_{BE}(\text{ON})$	$V_{CE}=2.5\text{V}, I_C=4.0\text{A}$		3.5		3.5	V
h_{FE}	$V_{CE}=4.0\text{V}, I_C=1.5\text{A}$	15	150	15	150	
h_{FE}	$V_{CE}=2.5\text{V}, I_C=4.0\text{A}$	2.0		2.0		
h_{fe}	$V_{CE}=4.0\text{V}, I_C=0.5\text{A}, f=50\text{kHz}$	20		20		
f_T	$V_{CE}=4.0\text{V}, I_C=0.5\text{A} (2\text{N}6473, 2\text{N}6474)$	4.0		4.0		MHz
f_T	$V_{CE}=4.0\text{V}, I_C=0.5\text{A} (2\text{N}6475, 2\text{N}6476)$	5.0		5.0		MHz
C_{ob}	$V_{CB}=10\text{V}, f=1.0\text{MHz}$		250		250	pF